

ABSTRACT OF THE DISCLOSURE

Via-shaped copper interconnect lines (2) buried in an interlayer insulating film (8) are connected to gate interconnect lines (1) in the lowermost layer. A copper interconnect line (6) of a shield ring (5) is buried in the interlayer insulating film (8),
5 closer to outside than the copper interconnect lines (2). A silicon nitride film (9) is provided on the via-shaped copper interconnect lines (2), on the copper interconnect line (6) of the shield ring (5), and on the interlayer insulating film (8). Provided on the silicon nitride film (9) is a silicon oxide film (10) which holds therein a fuse line (3) for connecting different ones of copper interconnect lines (2). The silicon oxide film (10) is
10 also provided on the upper surfaces of the fuse line (3) and the aluminum interconnect line (7). A silicon nitride film (11) is provided on the silicon oxide film (10). The silicon nitride film (11) defined over the fuse line (3) is removed, thereby creating an opening (4). The silicon nitride film (11) and the aluminum interconnect line (7) are directly connected.